

In the Claims:

1 1. (currently amended) A method of processing a surface of a  
2 nitride semiconductor crystal, wherein

3 a surface of a nitride semiconductor crystal ~~[(11)]~~  
4 is brought into contact with a liquid containing at least  
5 Na, Li or Ca as a processing ~~solution (15)~~. solution.

1 2. (currently amended) The method of processing a surface of  
2 a nitride semiconductor crystal according to claim 1,  
3 wherein

4 said processing solution ~~[(15)]~~ is a liquid  
5 containing at least Na and has an Na content of 5-95 mol%.

1 3. (currently amended) The method of processing a surface of a  
2 nitride semiconductor crystal according to claim 1, wherein

3 said processing solution ~~[(15)]~~ is a liquid  
4 containing at least Li and has an Li content of 5-100 mol%.

1 4. (currently amended) The method of processing a surface of  
2 a nitride semiconductor crystal according to claim 1,  
3 wherein

4 said nitride semiconductor crystal ~~[(11)]~~ is an  
5  $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$  semiconductor crystal ( $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  
6  $0 \leq x + y \leq 1$ ).

5. (currently amended) A nitride semiconductor crystal having a maximum depth of a surface scratch of at most 0.01  $\mu\text{m}$  and obtained with a method of processing a surface of a nitride semiconductor crystal wherein a surface of a nitride semiconductor crystal ~~[(11)]~~ is brought into contact with a liquid containing at least Na, Li or Ca as a processing ~~solution (15).~~ solution.

6. (currently amended) The nitride semiconductor crystal according to claim 5, wherein said processing solution ~~[(15)]~~ is a liquid containing at least Na and has an Na content of 5-95 mol%.

7. (currently amended) The nitride semiconductor crystal according to claim 5, wherein said processing solution ~~[(15)]~~ is a liquid containing at least Li and has an Li content of 5-100 mol%.

8. (currently amended) The nitride semiconductor crystal according to claim 5, wherein said nitride semiconductor crystal ~~[(11)]~~ is an  $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$  semiconductor crystal ( $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x + y \leq 1$ ).

9. (currently amended) A nitride semiconductor crystal having an average thickness of a damaged layer of at most 2  $\mu\text{m}$  and

3 obtained with a method of processing a surface of a nitride  
4 semiconductor crystal wherein a surface of a nitride  
5 semiconductor crystal ~~[(11)]~~ is brought into contact with  
6 a liquid containing at least Na, Li or Ca as a processing  
7 ~~solution (15).~~ solution.

1 10. (currently amended) The nitride semiconductor crystal  
2 according to claim 9, wherein

3 said processing solution ~~[(15)]~~ is a liquid  
4 containing at least Na and has an Na content of 5-95 mol%.

1 11. (currently amended) The nitride semiconductor crystal  
2 according to claim 9, wherein

3 said processing solution ~~[(15)]~~ is a liquid  
4 containing at least Li and has an Li content of 5-100 mol%.

1 12. (currently amended) The nitride semiconductor crystal  
2 according to claim 9, wherein

3 said nitride semiconductor crystal ~~[(11)]~~ is an  
4  $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$  semiconductor crystal ( $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  
5  $0 \leq x + y \leq 1$ ).

[AMENDMENT CONTINUES ON NEXT PAGE]